L Number	Hits	Search Text	DB	Time stamp
- Number	HITS 0	"20030030153"	USPAT	2004/07/11 19:09
1				
-	1	"20030030153"	USPAT;	2004/07/11 19:32
	_	W.CO. O. CO.	US-PGPUB	0004/07/11 10 11
-	2	"6018462"	USPAT;	2004/07/11 19:34
			US-PGPUB	
-	1		USPAT	2004/07/11 19:33
-	1		USPAT	2004/07/11 19:34
-	1		USPAT	2004/07/11 19:34
_	1		USPAT	2004/07/11 19:34
_	1		USPAT	2004/07/11 19:34
_	1039147	pad with multi\$4 with (under or lower)	USPAT;	2004/07/11 19:35
		layer	US-PGPUB	
_	1038997	pad with multi\$4 near (under or lower)	USPAT;	2004/07/11 19:36
	1000007	layer	US-PGPUB	======
 _	0	pad with multi\$4 near (under or_lower)	USPAT	2004/07/11 19:36
₩ [™]	·00 _		ODIAI .	2004/01/11 13:30
	33	near layers	TICDAT	2004/07/11 19:49
-	33	pad with multi\$4 with (under or lower)	USPAT	2004/0//11 19:49
]		near layers	Hanra	2004/07/11 22 12
-	1598	pad with multi\$4 near layers	USPAT	2004/07/11 20:10
-	47	(pad with multi\$4 near layers) and	USPAT	2004/07/11 20:10
		257/781		
-	9	"5378927"	USPAT	2004/07/11 20:00
-	203	pad with multi\$4 near layers with (solder	USPAT	2004/07/11 20:00
		or ball or bump)		
-	145	pad with multi\$4 near layers with (solder	USPAT	2004/07/11 20:01
1)		
_	26	(pad with multi\$4 near layers) and	USPAT	2004/07/11 20:12
	20	257/782		= = = = , = = , = =
1_	787	257/782	USPAT	2004/07/11 20:51
1 -	1296	257/779	USPAT	2004/07/11 20:51
1 -		,	USPAT	2004/07/11 20:52
-	1108	257/779 and solder	i i	2004/07/11 20:57
-	71	257/779 and solder and pad with (lower or	USPAT	2004/0//11 20:5/
		bottom or multi\$4) near (layer or film)	HODAE	2004/07/11 21:04
-	126	(257/779 or 257/780 or 257/781) and solder	USPAT	2004/07/11 21:04
		and pad with (lower or bottom or multi\$4)		
		near (layer or film)		0004/07/11 00 7
-	1		USPAT	2004/07/11 20:59
-	1		USPAT	2004/07/11 21:00
-	1		USPAT	2004/07/11 21:00
-	1		USPAT	2004/07/11 21:00
_	1		USPAT	2004/07/11 21:00
_	1		USPAT	2004/07/11 21:01
-	1		USPAT	2004/07/11 21:01
_	2029	(semiconductor or die or chip or IC) and	USPAT	2004/07/11 21:05
	= ===================================	pad with (lower or bottom or multi\$4) near		
		(layers or films)		
1_	1123	(semiconductor or die or chip or IC) and	USPAT	2004/07/11 22:05
-	1123	(semiconductor or die or chip or ic) and pad with multi\$4 near (layers or films)	OSERI	2004/07/11 22.05
		pau with multipa hear (layers of lilms)	HCDAT	2004/07/11 22:05
-	711	(semiconductor or die or chip or IC) and	USPAT	2004/07/11 22:05
	_	pad with two near (layers or films)	HODAE	2004/07/11 22:00
-	3		USPAT	2004/07/11 22:06
		pad with two near (lower or bottom) near		
		(layers or films)		
-	0		USPAT	2004/07/11 22:06
		pad with three near (lower or bottom) near		
	1	(layers or films)		
_	4		USPAT	2004/07/11 22:07
		pad with multi near (lower or bottom) near		
		(layers or films)	1	
_	834		USPAT	2004/07/11 22:08
-	634		33171	2004,01,11 22.00
L	L	pad with barrier near (layers or films)	1	I